

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In the Patent Application of:

Applicants: Tsutomu Tanaka, et al.

Application No.: 09/827,676

Confirmation No.: 6747

Filed: April 6, 2001

For: THIN-FILM TRANSISTOR AND METHOD FOR MAKING THE SAME

Group Art Unit: 2811

Examiner: Quang D.

AMENDMENT UNDER 37 C.F.R. § 1.111

Commissioner Of Patents and Trademarks
Washington, D.C. 20231

Sir:

In response to the Non-Final Office Action dated May 8, 2002, Paper No. 5, please amend the above-identified application as follows:

IN THE SPECIFICATION:

Page 6, please replace the second full paragraph, continuing to page 7, with the following new paragraph:

By setting the thickness of the protective insulating film 8 at 100 nm or less instead of approximately 200 nm in the process for fabricating the conventional bottom-gate TFT, and by injecting the dopant through the protective insulating film 8 when the LDD region 9, or the source-drain region 10 is formed subsequently, it is possible to eliminate the etching step of the protective insulating film 9 and also an insufficient breakdown voltage of the gate insulating film 6 can be overcome. Moreover, it has also been found that the structure of such a TFT or the method for fabricating the same can be employed for liquid crystal display devices and organic EL devices driven by TFTs.

IN THE CLAIMS:

Please enter the following amended claims:

4. (Amended) A method of making a bottom-gate thin-film transistor comprising: